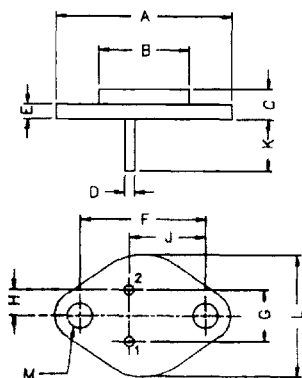


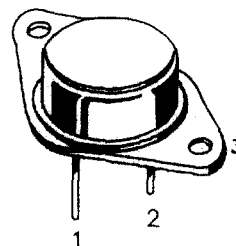
2SD350 NPN POWER TRANSISTOR

Horizontal Deflection Output Applications



ALL DIMENSIONS ARE IN M.M.

DIM	MIN	MAX
A	—	39,37
B	—	22,22
C	6,35	8,50
D	0,96	1,09
E	—	1,77
F	29,90	30,4
G	10,69	11,18
H	5,20	5,72
J	16,64	17,15
K	11,15	12,25
L	—	26,67
M	3,84	4,19



PIN CONFIGURATION

1. BASE
2. EMITTER
3. COLLECTOR

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)

 V_{CBO} max. 1500 V

Collector-emitter voltage (open base)

 V_{CEO} max. 700 V

Collector current

 I_C max. 5 ATotal power dissipation up to $T_C = 90^\circ\text{C}$ P_{tot} max. 35 W

Junction temperature

 T_j max. 200 $^\circ\text{C}$

Collector-emitter saturation voltage

 $I_C = 4.5\text{A}; I_B = 2\text{A}$ V_{CEsat} max. 5 V

D.C. current gain

 $I_C = 4\text{A}; V_{CE} = 10\text{V}$ h_{FE} min. 3.0
max. 8.0RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)

 V_{CBO} max. 1500 V

Collector-emitter voltage (open base)

 V_{CEO} max. 700 VCollector-emitter voltage ($V_{BE} \approx 0$) V_{CES} max. 1500 V

Emitter-base voltage (open collector)

 V_{EBO} max. 5 V

Collector current	I_C	max.	5 A
Collector current (peak)	I_{CP}	max.	7 A
Emitter current	I_E	max.	7.0 A
Total power dissipation up to $T_C = 90^\circ\text{C}$	P_{tot}	max.	35 W
Junction temperature	T_j	max.	200 $^\circ\text{C}$
Storage temperature	T_{stg}		-65 to +200 $^\circ\text{C}$

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0$; $V_{CB} = 750\text{V}$

I_{CBO} max. 100 μA

$I_E = 0$; $V_{CB} = 1500\text{V}$

I_{CBO} max. 1 mA

Breakdown voltages

$I_C = 1\text{ mA}$; $I_B = 0$

V_{CEO} min. 700 V

$I_C = 1\text{ mA}$; $I_E = 0$

V_{CBO} min. 1500 V

$I_E = 50\text{ mA}$; $I_C = 0$

V_{EBO} min. 5 V

Saturation voltages

$I_C = 4.5\text{A}$; $I_B = 2\text{A}$

V_{CEsat}^* max. 5.0 V

V_{BEsat}^* max. 1.6 V

D.C. current gain

$I_C = 4\text{A}$; $V_{CE} = 10\text{V}$

h_{FE}^* min. 3.0

max. 8.0

Switching time

$I_C = 4\text{A}$; $I_{B(end)} = 2.5\text{A}$;

$L_B = 10\mu\text{H}$

Fall time

t_f max. 1.0 μs

Storage time

t_s typ. 13 μs

* Pulse test.